

AOZ8320DI

One-Line Surge Protection High-Power TVS

General Description

The AOZ8320DI is a series of one-line, high-power transient voltage suppressor designed to protect power rail/bus from surge and ESD events, with an operating voltage range from 2.5V to 36V.

This device incorporates one unidirectional TVS diode in an ultra-small 1.6mm x 0.8mm DFN package. It may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (±15kV air, ±8kV contact discharge).

The AOZ8320DI comes in an RoHS compliant package and is rated over a -40°C to +125°C ambient temperature range.

Features

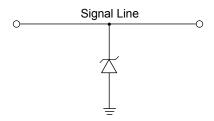
- Surge protection for power rail
- IEC 61000-4-5 8/20µs 22-85A
- IEC 61000-4-2 (ESD) ±30kV (air and contact)
- Human body model (HBM) ±30kV
- IEC 61000-4-4 (EFT) 80A (5/50ns)
- Peak pulse power 1100W to 1500W
- Operating voltage: 2.5V, 5V, 8V, 9V, 12V, 18V, 20V, 36V
- Green product

Applications

- USB voltage bus
- Battery protection
- Mobile devices
- Screen panels
- Other power rails

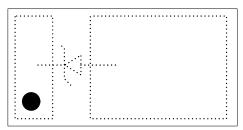


Typical Application



Unidirection Protection of Single Line

Pin Configuration



DFN1.6x0.8_2L (Top View)



Ordering Information

Part Number	Ambient Temperature Range	Package	Environmental
AOZ8320DI-02			
AOZ8320DI-05			
AOZ8320DI-08			
AOZ8320DI-09	-40°C to +125°C	1.6mm x 0.8mm DFN 2L	Green Product
AOZ8320DI-12	-40 C to +125 C	1.011111 X 0.0111111 DFN_2L	Green Floudci
AOZ8320DI-18			
AOZ8320DI-20			
AOZ8320DI-36			



AOS Green Products use reduced levels of Halogens, and are also RoHS compliant.

 $Please\ visit\ www.aosmd.com/media/AOSGreen Policy.pdf\ for\ additional\ information.$

Absolute Maximum Ratings

Exceeding the Absolute Maximum ratings may damage the device.

Parameter	Rating
VP-VN	2.5V to 36V
Peak Pulse Current (I _{PP}), t _P = 8/20μs	22A to 85A
Peak Pulse Power (P_{PP}), t_P = 8/20 μ s	1100W to 1500W
Storage Temperature (T _S)	-65°C to +150°C
ESD Rating per IEC61000-4-2, Contact ⁽¹⁾	±30kV
ESD Rating per IEC61000-4-2, Air ⁽¹⁾	±30kV
ESD Rating per Human Body Model ⁽²⁾	±30kV

Notes:

- 1. IEC 61000-4-2 discharge with C $_{Discharge}$ = 150pF, R $_{Discharge}$ = 330 $\!\Omega.$
- 2. Human Body Discharge per MIL-STD-883, Method 3015 $C_{Discharge}$ = 100pF, $R_{Discharge}$ = 1.5k Ω .

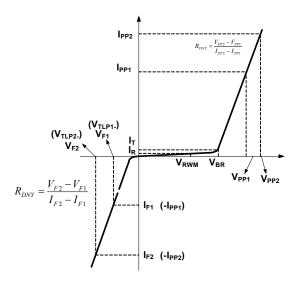
Maximum Operating Ratings

Parameter	Rating
Junction Temperature (T _J)	-40°C to +125°C

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Electrical Characteristics



 $T_A = 25$ °C unless otherwise specified.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
AOZ8320D	I-02					
V_{RWM}	Reverse Working Voltage	I/O Pin-to-Ground			2.5	V
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA, I/O Pin-to-Ground	2.8	3.3	5	V
I _R	Reverse Leakage Current	Max. V _{RWM} , I/O Pin-to-Ground		100	1000	nA
I _{PP}	Peak Pulse Current	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			75	Α
	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse,	I _{TLP} = 1A I _{TLP} = -1A		4.5 -1	6 -2	V
V	I/O Pin-to-Ground)	I _{TLP} = 30A I _{TLP} = -30A		5.5 -3.5	7.5 -5	V
V_{CL}	Clamping Voltage ⁽³⁾ (IEC61000-4-5 8/20µs, I/O Pin-to- Ground)	I _{PP} = 10A I _{PP} = -10A		5.5 -2.5	7.5 -4	V
		I _{PP} = 75A I _{PP} = -75A		13 -10	15 -12	V
R _{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 1A to 30A I _{TLP} = -1A to -30A		0.05 0.1		Ω
P _{PP}	Peak Pulse Power	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			1100	W
CJ	Junction Capacitance	V _{I/O} = 0V, f = 1MHz, I/O Pin-to-Ground		100		pF

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Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
AOZ8320D	I-05					
V _{RWM}	Reverse Working Voltage	I/O Pin-to-Ground			5	V
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA, I/O Pin-to-Ground	6	7.5	8.5	V
I _R	Reverse Leakage Current	Max. V _{RWM} , I/O Pin-to-Ground		100	1000	nA
I _{PP}	Peak Pulse Current	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			85	Α
	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse,	I _{TLP} = 1A I _{TLP} = -1A		8 -1	9.5 -2	V
V_{CL}	I/O Pin-to-Ground)	I _{TLP} = 30A I _{TLP} = -30A		9.5 -3.5	11 -5	V
V CL	Clamping Voltage ⁽³⁾ (IEC61000-4-5 8/20µs, I/O Pin-to-	I _{PP} = 20A I _{PP} = -20A		9.5 -2.5	11 -4	٧
	Ground)	I _{PP} = 85A I _{PP} = -85A		14.3 -6	16 -8	٧
R _{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 1A to 30A I _{TLP} = -1A to -30A		0.05 0.09		Ω
P _{PP}	Peak Pulse Power	IEC61000-4-5, 8/20µs, I/O Pin-to-Ground			1500	W
CJ	Junction Capacitance	V _{I/O} = 0V, f = 1MHz, I/O Pin-to-Ground		675		pF
AOZ8320D	N-08					
V _{RWM}	Reverse Working Voltage	I/O Pin-to-Ground			8	V
V_{BR}	Reverse Breakdown Voltage	I _T = 1mA, I/O Pin-to-Ground	9	10	12	V
I _R	Reverse Leakage Current	Max. V _{RWM} , I/O Pin-to-Ground		10	100	nA
I _{PP}	Peak Pulse Current	IEC61000-4-5, 8/20µs, I/O Pin-to-Ground			70	Α
	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse,	I _{TLP} = 1A I _{TLP} = -1A		10.5 -0.9	12 -1.5	V
V	I/O Pin-to-Ground)	I _{TLP} = 30A I _{TLP} = -30A		12 -3.7	13.5 -5	V
V_{CL}	Clamping Voltage ⁽³⁾	I _{PP} = 10A I _{PP} = -10A		12 -2.4	14 -4	V
	(IEC61000-4-5 8/20μs, I/O Pin-to- Ground)	I _{PP} = 70A I _{PP} = -70A		21 -9	24 -11	V
R _{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 1A to 30A I _{TLP} = -1A to -30A		0.05 0.1		Ω
P _{PP}	Peak Pulse Power	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			1500	W
CJ	Junction Capacitance	V _{I/O} = 0V, f = 1MHz, I/O Pin-to-Ground		425		pF

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Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
AOZ8320D	1-09					
V _{RWM}	Reverse Working Voltage	I/O Pin-to-Ground			9	٧
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA, I/O Pin-to-Ground	10	11	13	V
I _R	Reverse Leakage Current	Max. V _{RWM} , I/O Pin-to-Ground		10	100	nA
I _{PP}	Peak Pulse Current	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			65	Α
	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse,	I _{TLP} = 1A I _{TLP} = -1A		11.5 -0.9	13 -1.5	V
V_{CL}	I/O Pin-to-Ground)	I _{TLP} = 30A I _{TLP} = -30A		13.3 -3.7	15 -5	٧
▼ CL	Clamping Voltage ⁽³⁾ (IEC61000-4-5 8/20µs, I/O Pin-to-	I _{PP} = 10A I _{PP} = -10A		13.5 -2.4	15 -4.5	V
	Ground)	I _{PP} = 65A I _{PP} = -65A		21.5 -8.5	24 -10.5	V
R_{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 1A to 30A I _{TLP} = -1A to -30A		0.05 0.1		Ω
P _{PP}	Peak Pulse Power	IEC61000-4-5, 8/20µs, I/O Pin-to-Ground			1500	W
C_J	Junction Capacitance	V _{I/O} = 0V, f = 1MHz, I/O Pin-to-Ground		385		pF
AOZ8320D	l-12					
V_{RWM}	Reverse Working Voltage	I/O Pin-to-Ground			12	V
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA, I/O Pin-to-Ground	13.2	15	17	V
I _R	Reverse Leakage Current	Max. V _{RWM} , I/O Pin-to-Ground		5	100	nA
I _{PP}	Peak Pulse Current	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			45	Α
	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse,	I _{TLP} = 1A I _{TLP} = -1A		15.5 -0.9	18 -1.5	V
V	I/O Pin-to-Ground)	I _{TLP} = 30A I _{TLP} = -30A		17 -3.5	19 -5	V
V_{CL}	Clamping Voltage ⁽³⁾ (IEC61000-4-5 8/20µs, I/O Pin-to-	I _{PP} = 10A I _{PP} = -10A		18 -2.4	21 -4.5	V
	Ground)	I _{PP} = 45A I _{PP} = -45A		26 -6.8	30 -8.5	V
R _{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 1A to 30A I _{TLP} = -1A to -30A		0.05 0.1		Ω
P _{PP}	Peak Pulse Power	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			1500	W
CJ	Junction Capacitance	V _{I/O} = 0V, f = 1MHz, I/O Pin-to-Ground		275		pF

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Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
AOZ8320D	I-18					
V _{RWM}	Reverse Working Voltage	I/O Pin-to-Ground			18	V
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA, I/O Pin-to-Ground	19	21.5	24	V
I _R	Reverse Leakage Current	Max. V _{RWM} , I/O Pin-to-Ground		10	100	nA
I _{PP}	Peak Pulse Current	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			35	Α
	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse,	I _{TLP} = 1A I _{TLP} = -1A		22 -1	24 -2	V
V	I/O Pin-to-Ground)	I _{TLP} = 30A I _{TLP} = -30A		26 -4	29 -6	V
V_{CL}	Clamping Voltage ⁽³⁾ (IEC61000-4-5 8/20µs, I/O Pin-to-	I _{PP} = 10A I _{PP} = -10A		25 -2.5	29 -4.5	V
	Ground)	I _{PP} = 35A I _{PP} = -35A		35 -6	39 -8	V
R_{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 1A to 30A I _{TLP} = -1A to -30A		0.1 0.1		Ω
P _{PP}	Peak Pulse Power	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			1200	W
CJ	Junction Capacitance	V _{I/O} = 0V, f = 1MHz, I/O Pin-to-Ground		200		pF
AOZ8320D	I-20					
V _{RWM}	Reverse Working Voltage	I/O Pin-to-Ground			20	V
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA, I/O Pin-to-Ground	22	25	28	V
I _R	Reverse Leakage Current	Max. V _{RWM} , I/O Pin-to-Ground		2	100	nA
I _{PP}	Peak Pulse Current	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			32	Α
	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse,	I _{TLP} = 1A I _{TLP} = -1A		25.5 -0.9	28 -1.5	V
V	I/O Pin-to-Ground)	I _{TLP} = 30A I _{TLP} = -30A		29 -3.5	32 -5	V
V_{CL}	Clamping Voltage ⁽³⁾ (IEC61000-4-5 8/20µs, I/O Pin-to-	I _{PP} = 5A I _{PP} = -5A		28 -2	31 -4	٧
	Ground)	I _{PP} = 32A I _{PP} = -32A		40 -5.5	44 -7.5	٧
R_{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 1A to 30A I _{TLP} = -1A to -30A		0.12 0.1		Ω
P _{PP}	Peak Pulse Power	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			1200	W
CJ	Junction Capacitance	V _{I/O} = 0V, f = 1MHz, I/O Pin-to-Ground		165		pF

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Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
AOZ8320D	AOZ8320DI-36					
V _{RWM}	Reverse Working Voltage	I/O Pin-to-Ground			36	V
V_{BR}	Reverse Breakdown Voltage	I _T = 1mA, I/O Pin-to-Ground	37	39	44	V
I _R	Reverse Leakage Current	Max. V _{RWM} , I/O Pin-to-Ground		10	100	nA
I _{PP}	Peak Pulse Current	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			22	Α
	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse, I/O Pin-to-Ground)	I _{TLP} = 1A I _{TLP} = -1A		43 -1	47 -2	V
V		I _{TLP} = 30A I _{TLP} = -30A		52 -3.5	56 -5	V
V_{CL}	Clamping Voltage ⁽³⁾ (IEC61000-4-5 8/20µs, I/O Pin-to- Ground)	I _{PP} = 2A I _{PP} = -2A		45 -1.3	48 -2	V
		1 \ 1 \ - 22 \			72 -4.3	77 -7
R_{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 1A to 30A I _{TLP} = -1A to -30A		0.28 0.1		Ω
P _{PP}	Peak Pulse Power	IEC61000-4-5, 8/20μs, I/O Pin-to-Ground			1500	W
C_{J}	Junction Capacitance	V _{I/O} = 0V, f = 1MHz, I/O Pin-to-Ground		130		pF

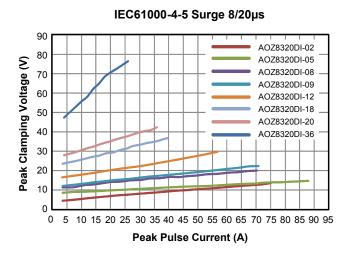
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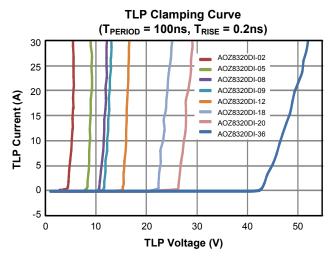
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 $[\]ensuremath{\mathtt{3}}.$ These specifications are guaranteed by design and characterization.



Typical Characteristics

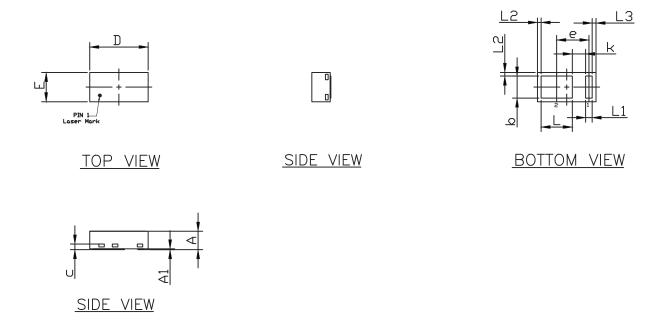




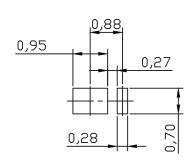
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Package Dimensions, DFN 1.6 x 0.8, 2L_EPS_S



RECOMMENDED LAND PATTERN



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CAMBEI C	DIMENS	DIMENSIONS IN MILLIMETERS			I NI ZNDIZN	INCHES
SYMBOLS	MIN	NDM	MAX	MIN	NDM	MAX
Α	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.55	0.60	0.65	0.022	0.024	0.026
С	0.15REF			0.006REF		
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.75	0.80	0.85	0.029	0.031	0.033
e		0.88BSC			0.035BSC	
L	0.80	0.85	0.90	0.031	0.033	0.035
L1	0.13	0.18	0.23	0.005	0.007	0.009
L2	0.05	0.10	0.15	0.002	0.004	0.006
L3	0.055	0.105	0.155	0.002	0.004	0.006
К	0.365REF				0.014REF	

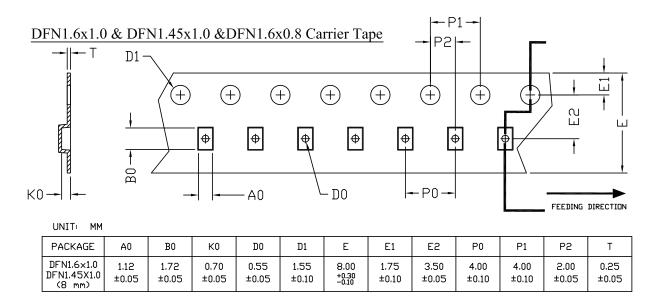
NOTE

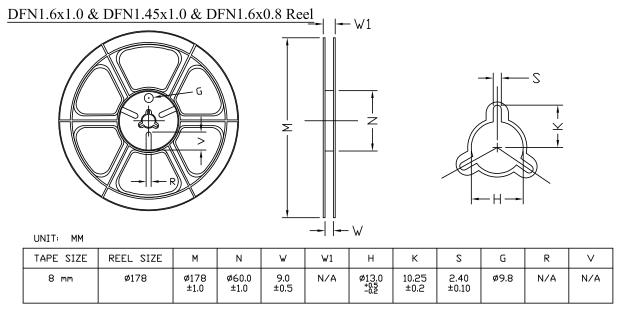
- 1. CONTROLLING DIMENSION IS MILLIMETER.

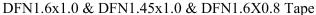
 CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
- 2. TOLERANCE :±0.05 UNLESS OTHERWISE SPECIFIED.
- 3. RADIUS ON ALL CORNER ARE 0.152 MAX., UNLESS OTHERWISE SPECIFIED.
- 4. PACKAGE WARPAGE: 0.012 MAX.
- 5. NO ANY PLASTIC FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.
- 6. PAD PLANARITY: ±0.102
- 7. CRACK BETWEEN PLASTIC BODY AND LEAD IS NOT ALLOWED.

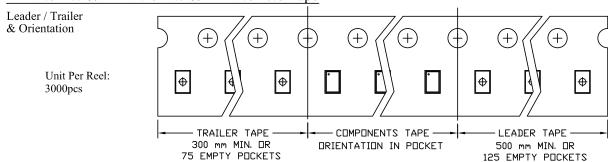


Tape and Reel Dimensions, DFN 1.6 x 0.8, 2L_EPS_S



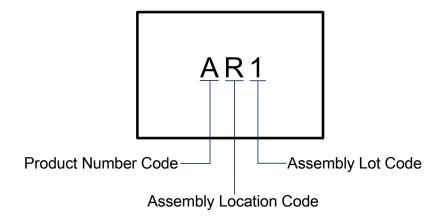








Part Marking



Part Number	Part Number Code of Marking
AOZ8320DI-02	В
AOZ8320DI-05	С
AOZ8320DI-08	D
AOZ8320DI-09	E
AOZ8320DI-12	F
AOZ8320DI-18	G
AOZ8320DI-20	Н
AOZ8320DI-36	К

LEGAL DISCLAIMER

Applications or uses as critical components in life support devices or systems are not authorized. AOS does not assume any liability arising out of such applications or uses of its products. AOS reserves the right to make changes to product specifications without notice. It is the responsibility of the customer to evaluate suitability of the product for their intended application. Customer shall comply with applicable legal requirements, including all applicable export control rules, regulations and limitations.

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LIFE SUPPORT POLICY

ALPHA AND OMEGA SEMICONDUCTOR PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS.

As used herein:

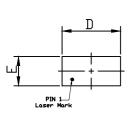
- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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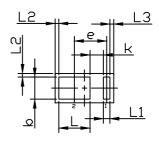


Document No.	PO-00274
Version	А

DFN1.6x0.8_2L_EP2_S PACKAGE OUTLINE



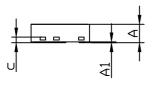




TOP VIEW

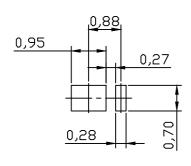
SIDE VIEW

BOTTOM VIEW



SIDE VIEW

RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.45	0.50	0.55	0.018	0.020	0.022	
A1	0.00	0.02	0.05	0.000	0.001	0.002	
b	0.55	0.60	0.65	0.022	0.024	0.026	
С	0.15REF			0.006REF			
D	1.55	1.60	1.65	0.061	0.063	0.065	
E	0.75	0.80	0.85	0.029	0.031	0.033	
е	0.88B2C			0.035BSC			
L	0.80	0.85	0.90	0.031	0.033	0.035	
L1	0.13	0.18	0.23	0.005	0.007	0.009	
L2	0.05	0.10	0.15	0.002	0.004	0.006	
L3	0.055	0.105	0.155	0.002	0.004	0.006	
К	0.365REF			0.014REF			

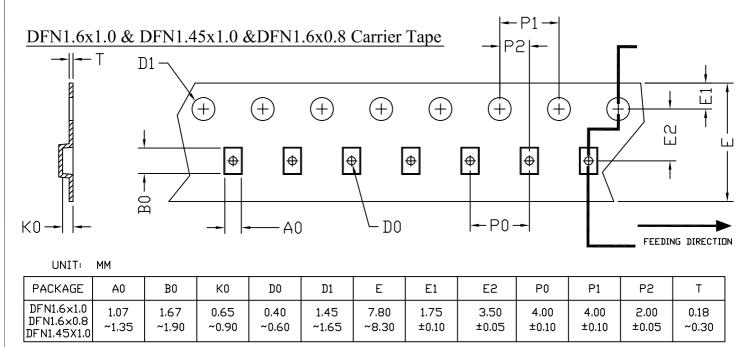
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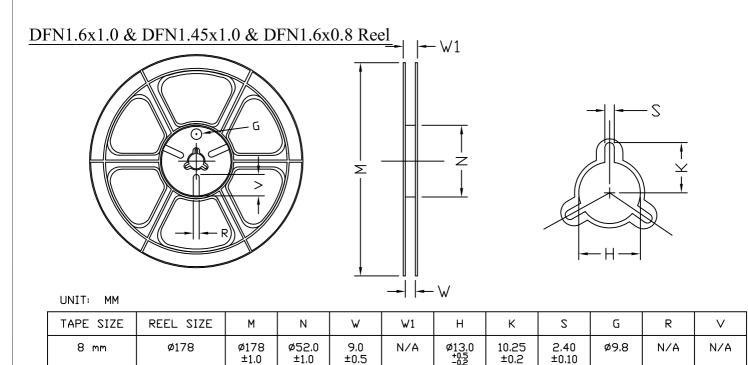
NOTE

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- 3. RADIUS ON ALL CORNER ARE 0.152 MAX., UNLESS OTHERWISE SPECIFIED.
- 4. PACKAGE WARPAGE: 0.012 MAX.
- 5. NO ANY PLASTIC FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.
- 6. PAD PLANARITY: ±0.102
- 7. CRACK BETWEEN PLASTIC BODY AND LEAD IS NOT ALLOWED.

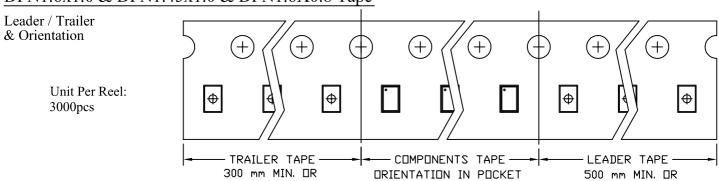


DFN1.6x1.0 & DFN1.45x1.0 & DFN1.6x0.8 Tape and Reel Data





DFN1.6x1.0 & DFN1.45x1.0 & DFN1.6X0.8 Tape





AOS Semiconductor Product Reliability Report

AOZ8320DI-05, rev A

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc www.aosmd.com



This AOS product reliability report summarizes the qualification result for AOZ8320DI-05. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOZ8320DI-05 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTRB	Temp = 150°C , Vdd=100% of VRWMmax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
Precondition (Note A)	168hr 85°C / 85%RH + 3 cycle reflow@260°C	-	1386 pcs	0	JESD22-A113
HAST	130°C , 85%RH, 33.3 psia, Vdd = 80% of VRWMmax	96 hours	462 pcs	0	JESD22-A110
Autoclave	121°C , 29.7psia, RH=100%	96 hours	462 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air	250 / 500 cycles	462 pcs	0	JESD22-A104

Note: The reliability data presents total of available generic data up to the published date. Note A: MSL (Moisture Sensitivity Level) 1 based on J-STD-020

II. Reliability Evaluation

FIT rate (per billion): 7.63

MTTF = 14960 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate =
$$\text{Chi}^2 \times 10^9 / [2 \text{ (N) (H) (Af)}] = 7.63$$

MTTF = $10^9 / \text{FIT} = 14960 \text{ years}$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from burn-in tests

H = Duration of burn-in testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = Exp [Ea / k (1/Tj u - 1/Tj s)]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C + 273.16

k = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K